

ABSTRACT

When a semiconductor light emitting device or a semiconductor device is manufactured by growing
5 nitride III-V compound semiconductor layers, which will
form a light emitting device structure or a device
structure, on a nitride III-V compound semiconductor
substrate composed of a first region in form of a
10 crystal having a first average dislocation density and
a plurality of second regions having a second average
dislocation density higher than the first average
dislocation density and periodically aligned in the
first region, device regions are defined on the nitride
15 III-V compound semiconductor substrate such that the
device regions do not substantially include second
regions, emission regions or active regions of devices
finally obtained do not include second regions.